SiA110DJ

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Vishay Siliconix





 $\begin{tabular}{|c|c|c|c|} \hline PRODUCT SUMMARY \\ \hline V_{DS} (V) & 100 \\ \hline R_{DS(on)} max. (\Omega) at V_{GS} = 10 V & 0.055 \\ \hline R_{DS(on)} max. (\Omega) at V_{GS} = 7.5 V & 0.072 \\ \hline Q_g typ. (nC) & 6.5 \\ \hline I_D (A) ^a & 12 \\ \hline Configuration & Single \\ \hline \end{tabular}$

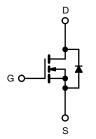
FEATURES

N-Channel 100 V (D-S) MOSFET

- TrenchFET[®] Gen IV power MOSFET
- Tuned for the lowest R_{DS} Q_{oss}
- 100% R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Primary side switch
- DC/DC converter
- Motor drive switch
- Boost converter
- LED backlighting



N-Channel MOSFET

ORDERING INFORMATION			
Package	PowerPAK SC-70		
Lead (Pb)-free and halogen-free	SiA110DJ-T1-GE3		

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	100	V	
Gate-source voltage		V _{GS}	± 20		
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		12 ^a		
	T _C = 70 °C		10		
	T _A =25 °C	I _D	5.4 ^{b, c}		
	T _A = 70 °C		4.3 ^{b, c}		
Pulsed drain current (t = 100 μs)		I _{DM}	20	A	
Continuous source-drain diode current	T _C = 25 °C		12 ^a		
	T _A = 70 °C	I _S	2.9 ^{b, c}		
Single pulse avalanche current		I _{AS}	10		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	5	mJ	
Maximum power dissipation	T _C = 25 °C		19		
	T _C = 70 °C		12	14/	
	T _A = 25 °C	P _D	3.5 ^{b, c}	W	
	T _A = 70 °C	1	2.2 ^{b, c}		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	*0	
Soldering recommendations (peak temperature) ^{d, e}			260	°C	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT		
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C/W		
Maximum junction-to-case (drain)	Steady state	R _{thJC}	5.3	6.5	C/W		

Notes

a. Package limited

b. Surface mounted on 1" x 1" FR4 board

c. t = 5 s

d. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

f. Maximum under steady state conditions is 80 °C/W

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Document Number: 76002

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COMPLIANT

HALOGEN

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SiA110DJ

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = 250 \mu A$	100	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	l _D = 10 mA	-	57	-		
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-7.2	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	2	-	4	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	100	nA	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA	
		$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 70 ^{\circ}\text{C}$	-	-	10		
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10$ V, $V_{GS} = 10$ V	10	-	-	Α	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4 \text{ A}$	-	0.046	0.055	Ω	
		$V_{GS} = 7.5 \text{ V}, I_D = 4 \text{ A}$	-	0.051	0.072		
Forward transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	25	-	S	
Dynamic ^b				•			
Input capacitance	C _{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz	-	550	-	pF	
Output capacitance	C _{oss}		-	50	-		
Reverse transfer capacitance	C _{rss}		-	7	-		
Tatal asta akawa	0	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$	-	8.5	13	nC	
Total gate charge	Qg		-	6.5	10		
Gate-source charge	Q _{gs}	V_{DS} = 50 V, V_{GS} = 7.5 V, I_D = 4 A	-	2.5	-		
Gate-drain charge	Q _{gd}		-	1.5	-		
Output charge	Q _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$	-	8	-		
Gate resistance	Rg	f = 1 MHz	0.3	1.3	2.6	Ω	
Turn-on delay time	t _{d(on)}		-	10	20	-	
Rise time	t _r	$\label{eq:VDD} \begin{split} V_{DD} = 50 \text{ V}, \text{R}_{L} = 12.5 \ \Omega, \text{I}_{D} \cong 4 \text{ A}, \\ V_{GEN} = 10 \text{ V}, \text{R}_{g} = 1 \ \Omega \end{split}$	-	5	10		
Turn-off delay time	t _{d(off)}		-	14	30		
Fall time	t _f		-	5	10		
Turn-on delay time	t _{d(on)}		-	11	20	ns	
Rise time	tr	$\label{eq:VDD} \begin{split} V_{DD} = 50 \text{ V}, \text{R}_{\text{L}} = 12.5 \ \Omega, \text{I}_{\text{D}} \cong 4 \text{ A}, \\ $	-	5	10	-	
Turn-off delay time	t _{d(off)}		-	14	30		
Fall time	t _f		-	5	10		
Drain-Source Body Diode Characterist	cs		•	•	•		
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	12	^	
Pulse diode forward current	I _{SM}		-	-	20	A	
Body diode voltage	V _{SD}	$I_{S} = 4 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.85	1.2	V	
Body diode reverse recovery time	t _{rr}		-	50	100	ns	
Body diode reverse recovery charge	Q _{rr}		-	55	110	nC	
Reverse recovery fall time	t _a	$I_F = 4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^\circ\text{C}$	-	27	-	ns	
Reverse recovery rise time	t _b		-	23	-		

Notes

a. Pulse test: pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

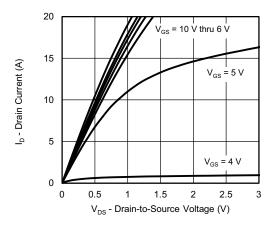
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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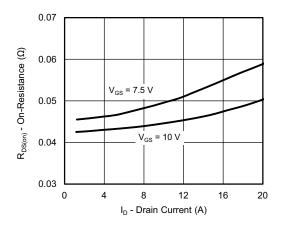
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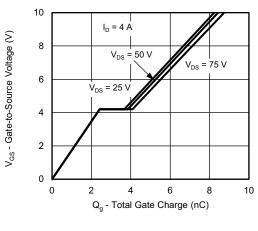
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



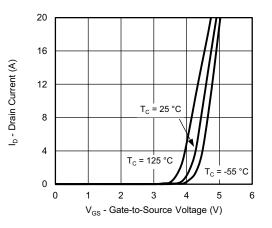
Output Characteristics



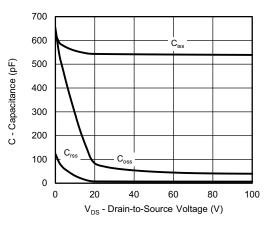
On-Resistance vs. Drain Current and Gate Voltage



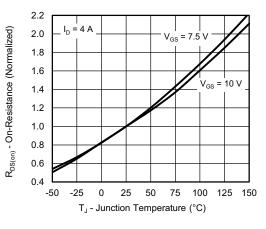
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

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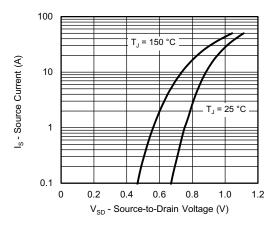
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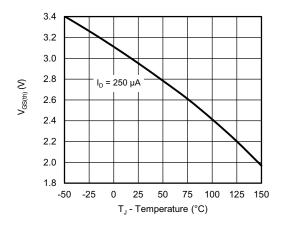
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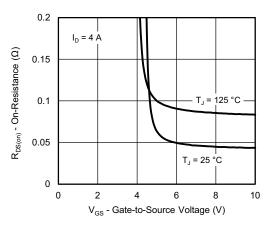
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



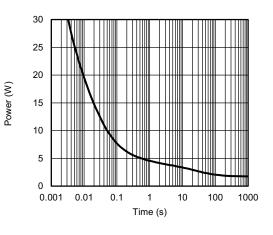
Source-Drain Diode Forward Voltage



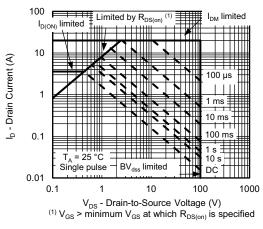
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

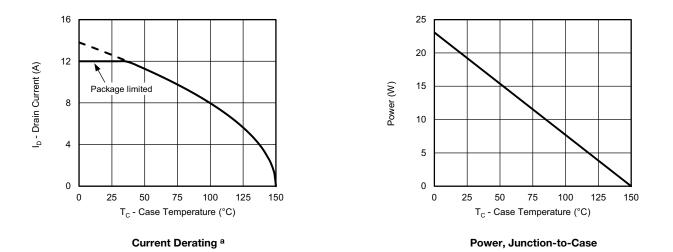
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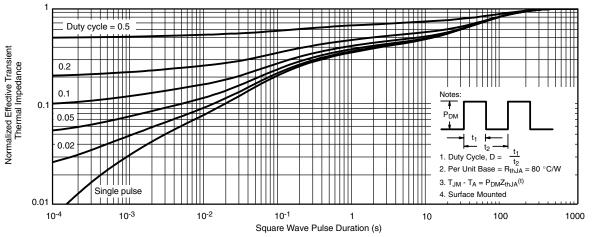


Note

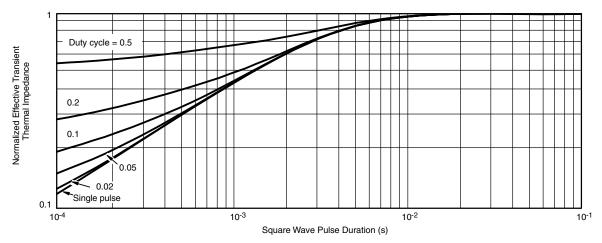
a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

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¹



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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